

ABSTRACT

A method for manufacturing an integrated circuit structure includes providing a semiconductor substrate and forming a thyristor thereon. The thyristor has at least four layers, with three P-N junctions therebetween. At least two of the layers are formed horizontally and at least two of the layers are formed vertically. A gate is formed adjacent at
5 least one of the vertically formed layers. An access transistor is formed on the semiconductor substrate, and an interconnect is formed between the thyristor and the access transistor.